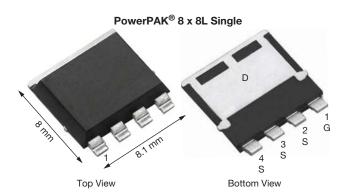
www.vishay.com

Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET



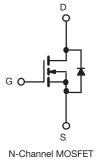
PRODUCT SUMMARY	
V _{DS} (V)	40
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0012
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0015
I _D (A)	200
Configuration	Single
Package	PowerPAK 8 x 8L

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Fully lead (Pb)-free device
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



FREE



ABSOLUTE MAXIMUM RATINGS (T	_C = 25 °C, unles	s otherwise noted	l)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage	V _{DS}	40	v		
Gate-source voltage	V _{GS}	V _{GS} ± 20			
Continuous drain current	T _C = 25 °C ª	1	200		
Continuous drain current	T _C = 125 °C	I _D	141		
Continuous source current (diode conduction)		ا _S	136	А	
Pulsed drain current ^b		I _{DM}	600		
Single pulse avalanche current		I _{AS}	50		
Single pulse avalanche energy	L = 0.1 mm	E _{AS}	125	mJ	
Maximum newer discinction	T _C = 25 °C	D	150	W	
Maximum power dissipation	T _C = 125 °C	P _D	50		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) d, e			260		

THERMAL RESISTANCE RATINGS PARAMETER SYMBOL LIMIT UNIT Junction-to-ambient PCB mount ^c R_{thJA} 50 °C/W 1 Junction-to-case (drain) R_{thJC}

Notes

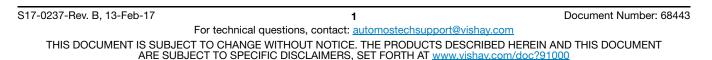
a. Package limited

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components





Vishay Siliconix

PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static		•						
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		40	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.5	2	2.5	v	
Gate-source leakage	I _{GSS}	V _{DS} =	= 0 V, V_{GS} = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1		
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS}=40~V,~T_J=125~^\circ C$	-	-	50	μA	
ate-source leakage ero gate voltage drain current n-state drain current ^a rain-source on-state resistance ^a prward transconductance ^b ynamic ^b put capacitance utput capacitance everse transfer capacitance otal gate charge ^c ate-source charge ^c		$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	500	1	
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	100	-	-	А	
Drain-source on-state resistance ^a		$V_{GS} = 10 \text{ V}$	I _D = 20 A	-	0.0009	0.0012		
	В	$V_{GS} = 4.5 V$	I _D = 10 A	-	0.0011	0.0015	Ω	
	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 20 A, T _J = 125 °C	-	-	0.0018		
		$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	0.0022					
Forward transconductance b	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 15 \text{ A}$		-	122	-	S	
Dynamic ^b								
Input capacitance	C _{iss}			-	10 810	14 500		
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	6500	8500	pF	
Reverse transfer capacitance	C _{rss}			-	700	950		
Total gate charge ^c	Qg		$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	-	140	220	nC	
Gate-source charge ^c	Q _{gs}	$V_{GS} = 10 V$		-	30	-		
Gate-drain charge ^c	Q _{gd}			-	20	-		
Gate resistance	Rg	f = 1 MHz		0.45	0.99	1.50	Ω	
Turn-on delay time ^c	t _{d(on)}			-	24	40		
Rise time ^c	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 2 \Omega$ $I_{D} \cong 10 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	60	100	- ns	
Turn-off delay time ^c	t _{d(off)}			-	60	100		
Fall time ^c	t _f			-	30	50		
Source-Drain Diode Ratings and Cha	aracteristics ^b							
Pulsed current ^a	I _{SM}			-	-	200	Α	
Forward voltage	V _{SD}	le :	= 50 A, V _{GS} = 0	-	0.8	1.2	V	

Notes

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

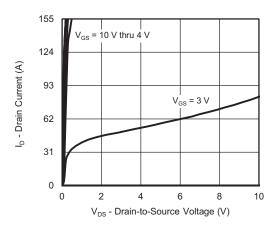
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

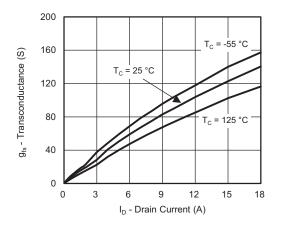


Vishay Siliconix

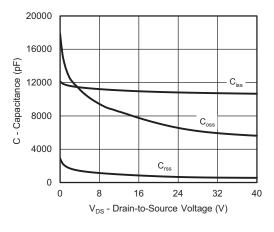
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



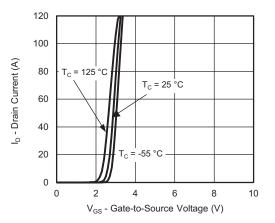
Output Characteristics



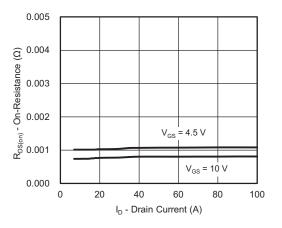
Transconductance



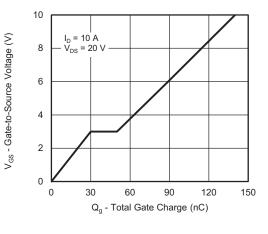
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

S17-0237-Rev. B, 13-Feb-17

3

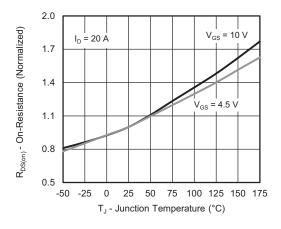
Document Number: 68443

For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

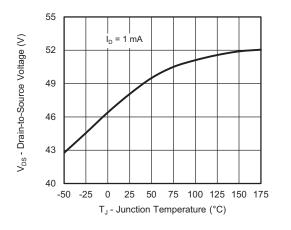


Vishay Siliconix

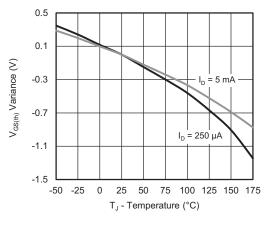
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



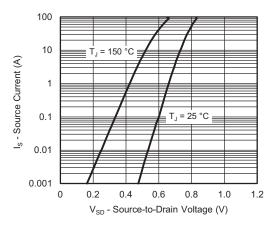
On-Resistance vs. Junction Temperature



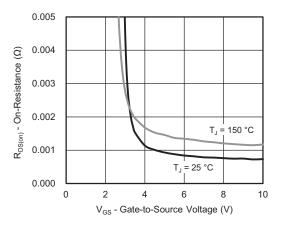
Drain Source Breakdown vs. Junction Temperature



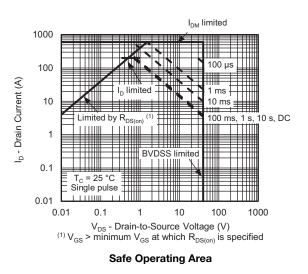
Threshold Voltage



Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



S17-0237-Rev. B, 13-Feb-17

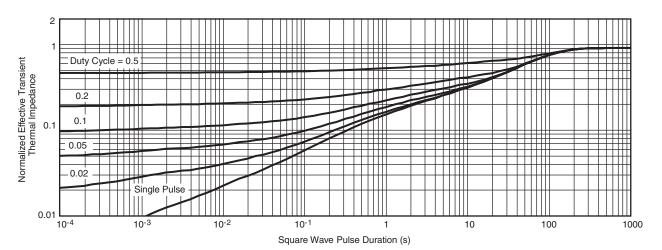
4 stions, contact: automostechsupp Document Number: 68443

For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

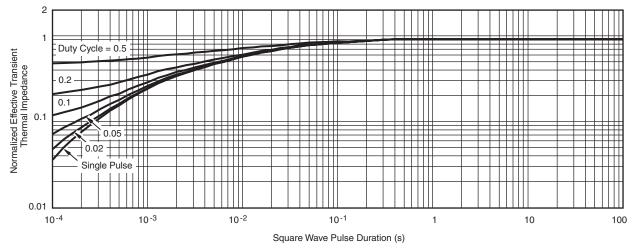


Vishay Siliconix

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



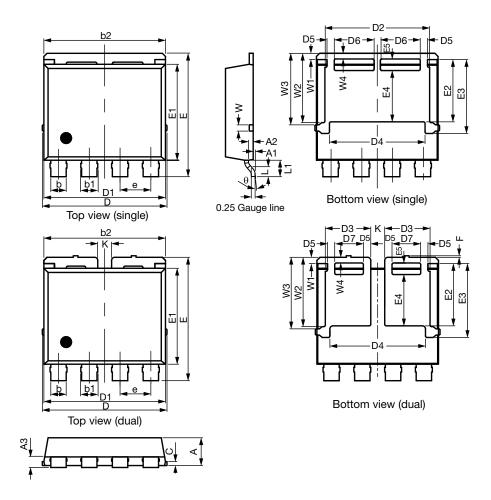
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?68443.



Vishay Siliconix





DIM.		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.70	1.80	1.90	0.067	0.071	0.075	
A1	0.00	0.08	0.13	0.000	0.003	0.005	
A2	0.25	0.30	0.35	0.010	0.012	0.014	
A3	0.55	0.62	0.70	0.022	0.024	0.028	
b	0.92	1.00	1.08	0.036	0.039	0.043	
b1	1.02	1.10	1.18	0.040	0.043	0.046	
b2	7.80	7.90	8.00	0.307	0.311	0.315	
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	8.00	8.10	8.25	0.315	0.319	0.325	
D1	7.80	7.90	8.00	0.307	0.311	0.315	
D2	6.70	6.80	6.90	0.264	0.268	0.272	
D3	2.85	2.95	3.05	0.112	0.116	0.120	
D4	6.11	6.21	6.31	0.241	0.244	0.248	
D5	0.37	0.47	0.57	0.015	0.019	0.022	
D6	2.49	2.59	2.69	0.098	0.102	0.106	
D7	1.76	1.86	1.96	0.069	0.073	0.077	

Revision: 16-Oct-17

Document Number: 67734

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

Package Information





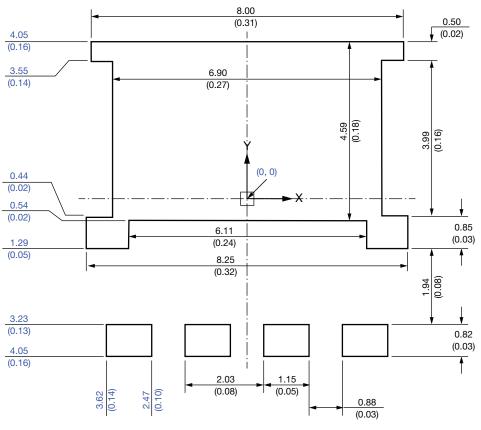
Vishay Siliconix

DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
е	1.95	2.00	2.05	0.077	0.079	0.081	
Е	7.90	8.00	8.10	0.311	0.315	0.319	
E1	6.12	6.22	6.32	0.241	0.245	0.249	
E2	3.94	4.04	4.14	0.140	0.159	0.163	
E3	4.69	4.79	4.89	0.185	0.189	0.193	
E4	3.23	3.33	3.43	0.127	0.131	0.135	
E5	0.65	0.75	0.85	0.026	0.030	0.033	
F	0.00	0.10	0.15	0.000	0.004	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К	0.80	0.90	1.00	0.031	0.035	0.039	
W	0.30	0.40	0.50	0.012	0.016	0.020	
W1	0.30	0.40	0.50	0.012	0.016	0.020	
W2	4.39	4.49	4.59	0.173	0.177	0.181	
W3	4.54	4.64	4.74	0.179	0.183	0.187	
W4	0.32	0.37	0.42	0.013	0.015	0.017	
θ	6°	10°	14°	6°	10°	14°	



Vishay Siliconix

Recommended Minimum PADs for PowerPAK® 8 x 8L Single



Dimensions in millimeters (inches)

Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2024 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

Revision: 01-Jan-2024